

Product Summary

| BV _{DSS} | R _{DS(ON)} max | I _D max T _A = +25°C |
|-------------------|-------------------------------|--|
| 30V | 21mΩ @ V _{GS} = 10V | 8.5A |
| | 35mΩ @ V _{GS} = 4.5V | 6.6A |

Description

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP.

Applications

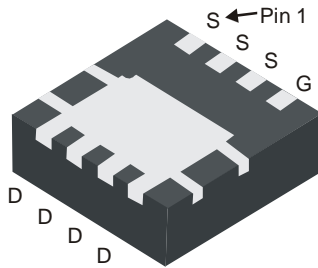
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

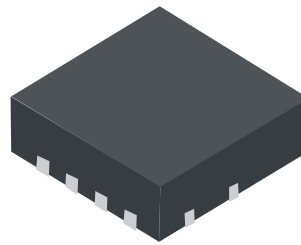
- Low R_{DS(ON)} – ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Mechanical Data

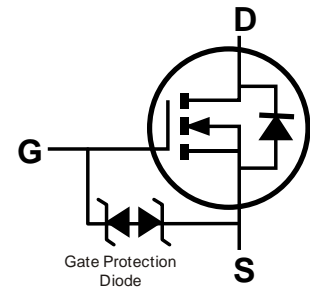
- Case: POWERDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.072 grams (Approximate)



Bottom View



Top View



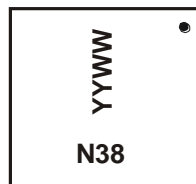
Top View
Internal Schematic

Ordering Information (Note 5)

| Part Number | Case | Packaging |
|----------------|----------------|------------------|
| DMN3018SFGQ-7 | POWERDI®3333-8 | 2000/Tape & Reel |
| DMN3018SFGQ-13 | POWERDI®3333-8 | 3000/Tape & Reel |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
 5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



N38 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 11 = 2011)
WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Unit |
|--|--------------|--|------------------|-------------|------|
| Drain-Source Voltage | | | V _{DSS} | 30 | V |
| Gate-Source Voltage | | | V _{GSS} | ±25 | V |
| Continuous Drain Current (Note 7) V _{GS} = 10V | Steady State | T _A = +25°C T _A = +70°C | I _D | 8.5 6.8 | A |
| | t < 10s | T _A = +25°C T _A = +70°C | I _D | 11.3 9.1 | A |
| Continuous Drain Current (Note 7) V _{GS} = 4.5V | Steady State | T _A = +25°C T _A = +70°C | I _D | 6.6 5.3 | A |
| | t < 10s | T _A = +25°C T _A = +70°C | I _D | 8.7 7.0 | A |
| Maximum Continuous Body Diode Forward Current (Note 7) | | | I _S | 2.5 | A |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) | | | I _{DM} | 60 | A |
| Avalanche Current (Note 8) L = 0.1mH | | | I _{AS} | 18 | A |
| Avalanche Energy (Note 8) L = 0.1mH | | | E _{AS} | 16 | mJ |

Thermal Characteristics

| Characteristic | | Symbol | Value | Unit |
|--|--------------|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 6) | | P _D | 1.0 | W |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | R _{θJA} | 126 | °C/W |
| | t < 10s | | 71 | |
| Total Power Dissipation (Note 7) | | P _D | 2.2 | W |
| Thermal Resistance, Junction to Ambient (Note 7) | Steady State | R _{θJA} | 56 | °C/W |
| | t < 10s | | 31 | |
| Thermal Resistance, Junction to Case | | R _{θJC} | 7.0 | |
| Operating and Storage Temperature Range | | T _J , T _{STG} | -55 to +150 | °C |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|--|---------------------|-----|------|-----|------|---|
| OFF CHARACTERISTICS (Note 9) | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 30 | — | — | V | V _{GS} = 0V, I _D = 250µA |
| Zero Gate Voltage Drain Current | I _{DSS} | — | — | 1 | µA | V _{DS} = 24V, V _{GS} = 0V |
| Gate-Source Leakage | I _{GSS} | — | — | ±10 | µA | V _{GS} = ±20V, V _{DS} = 0V |
| ON CHARACTERISTICS (Note 9) | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | 1 | 1.7 | 2.1 | V | V _{DS} = V _{GS} , I _D = 250µA |
| Static Drain-Source On-Resistance | R _{DS(ON)} | — | 16 | 21 | mΩ | V _{GS} = 10V, I _D = 10A |
| | | — | 21 | 35 | | V _{GS} = 4.5V, I _D = 8.5A |
| Diode Forward Voltage | V _{SD} | 0.5 | — | 1.2 | V | V _{GS} = 0V, I _S = 1A |
| DYNAMIC CHARACTERISTICS (Note 10) | | | | | | |
| Input Capacitance | C _{iss} | — | 697 | — | pF | V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz |
| Output Capacitance | C _{oss} | — | 97 | — | pF | |
| Reverse Transfer Capacitance | C _{rss} | — | 67 | — | pF | |
| Gate Resistance | R _g | — | 1.47 | — | Ω | V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz |
| Total Gate Charge (V _{GS} = 4.5V) | Q _g | — | 6.0 | — | nC | V _{GS} = 10V, V _{DS} = 15V, I _D = 9A |
| Total Gate Charge (V _{GS} = 10V) | Q _g | — | 13.2 | — | nC | |
| Gate-Source Charge | Q _{gs} | — | 2.2 | — | nC | |
| Gate-Drain Charge | Q _{gd} | — | 1.8 | — | nC | V _{DD} = 15V, V _{GS} = 10V, R _L = 15Ω, I _D = 1A, R _G = 6Ω |
| Turn-On Delay Time | t _{D(ON)} | — | 4.3 | — | ns | |
| Turn-On Rise Time | t _R | — | 4.4 | — | ns | |
| Turn-Off Delay Time | t _{D(OFF)} | — | 20.1 | — | ns | I _F = 9A, di/dt = 500A/µs |
| Turn-Off Fall Time | t _F | — | 4.1 | — | ns | |
| Reverse Recovery Time | t _{RR} | — | 7.3 | — | ns | |
| Reverse Recovery Charge | Q _{RR} | — | 7.9 | — | nC | |

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

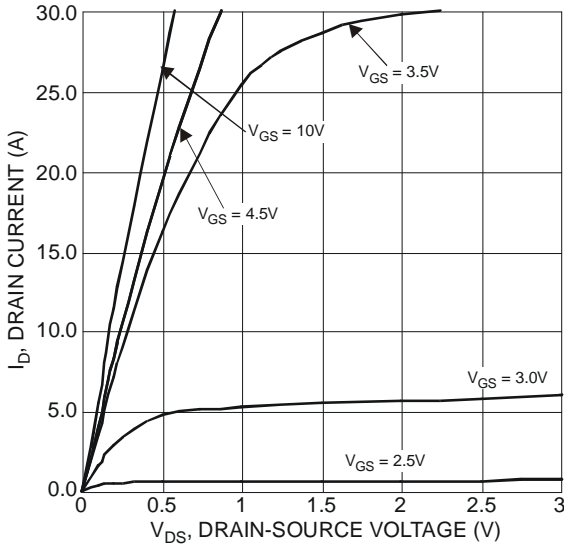


Figure 1 Typical Output Characteristics

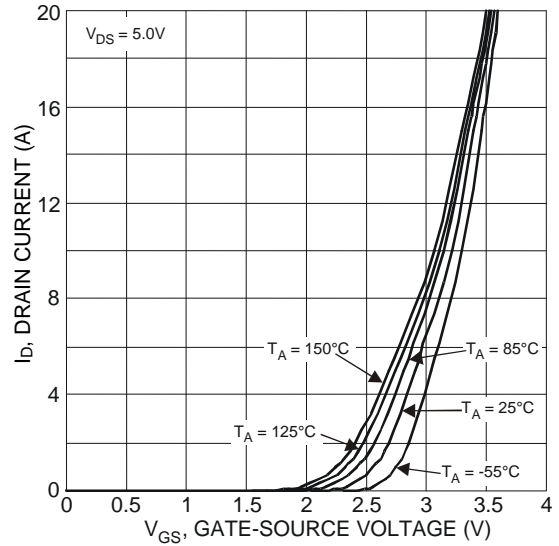


Figure 2 Typical Transfer Characteristics

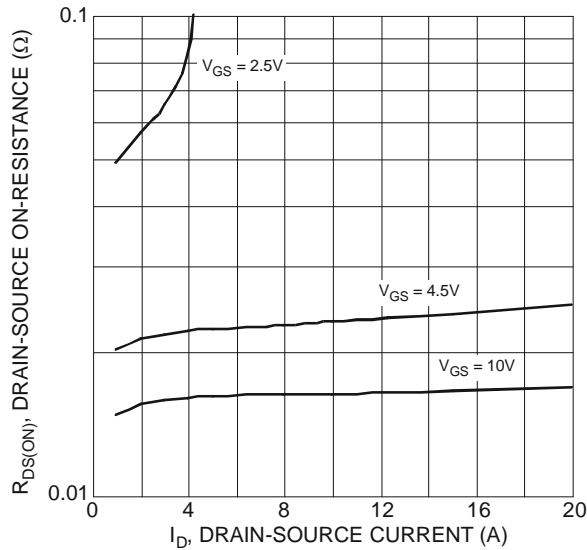


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

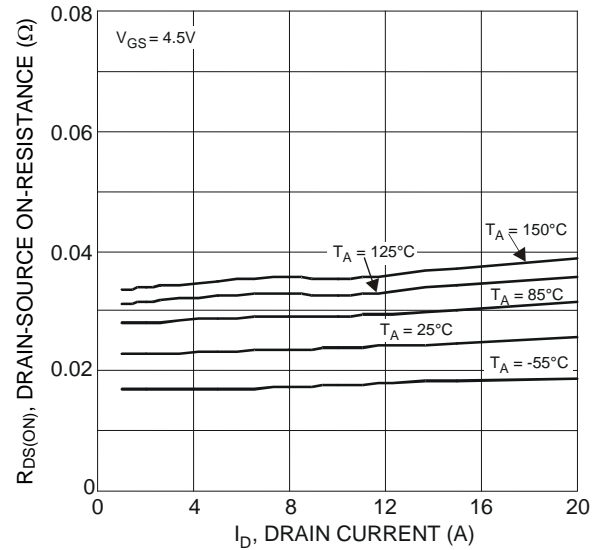


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

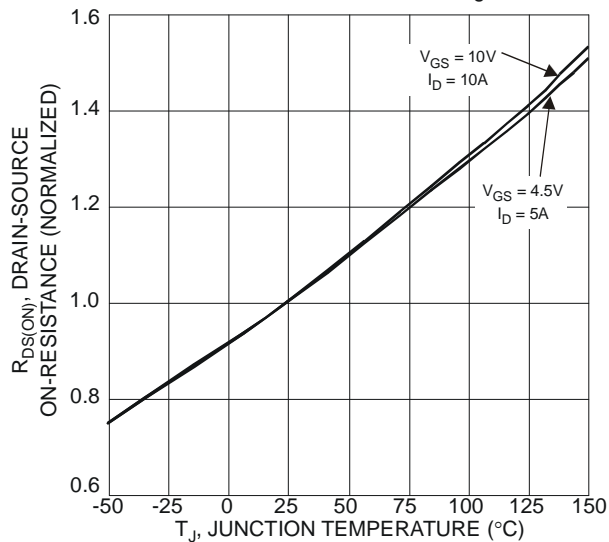


Figure 5 On-Resistance Variation with Temperature

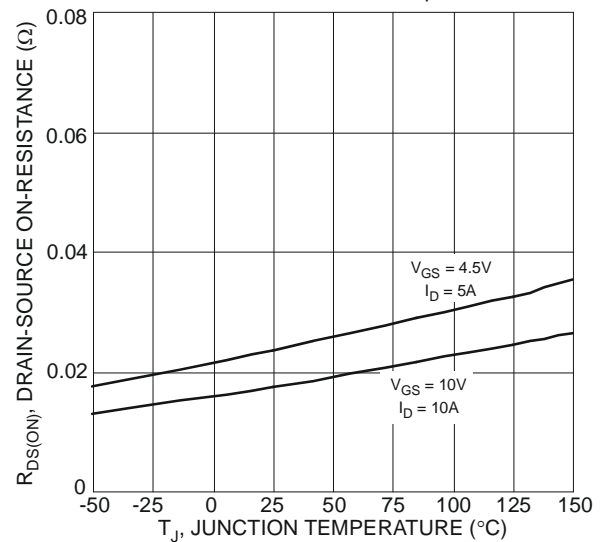


Figure 6 On-Resistance Variation with Temperature

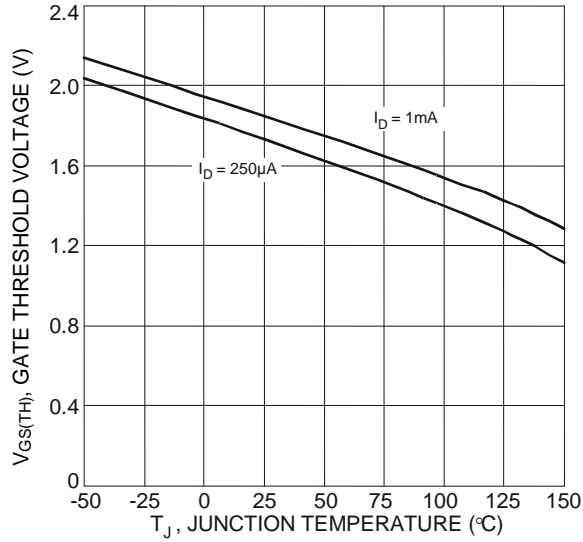


Figure 7 Gate Threshold Variation vs. Junction Temperature

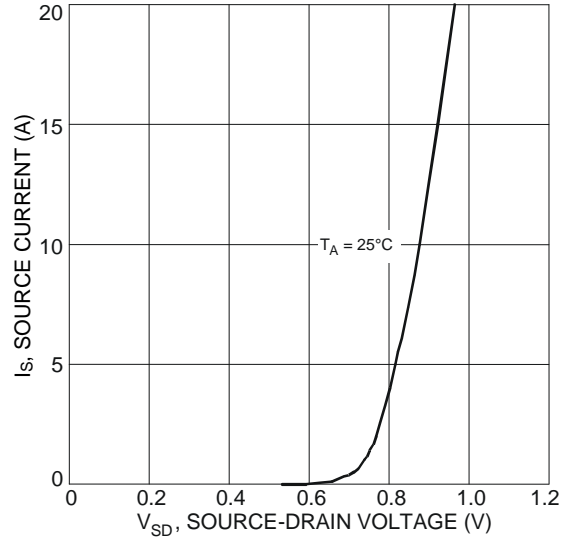


Figure 8 Diode Forward Voltage vs. Current

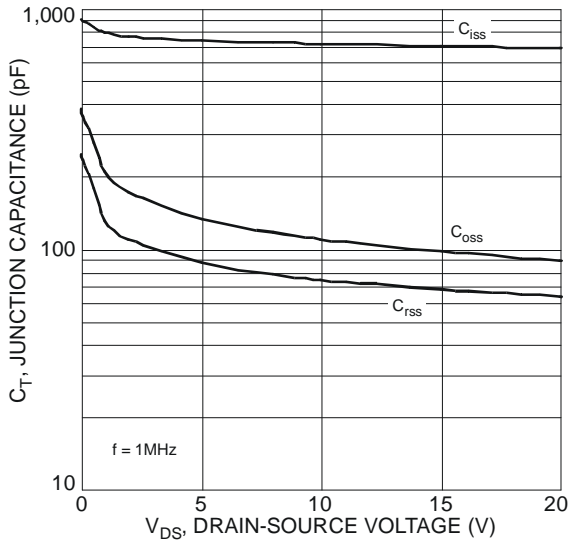


Figure 9 Typical Junction Capacitance

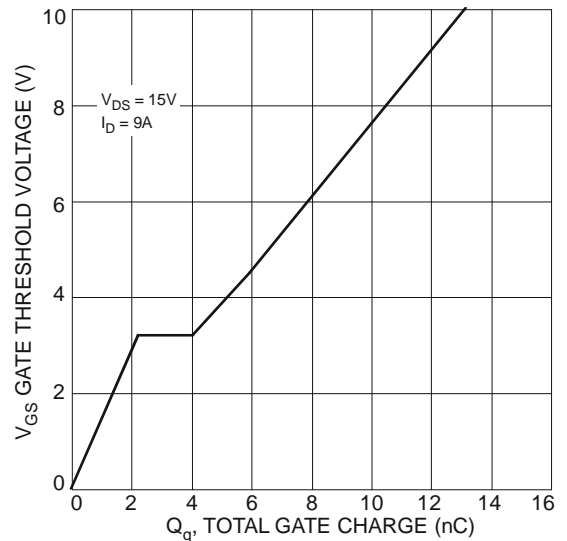


Figure 10 Gate Charge

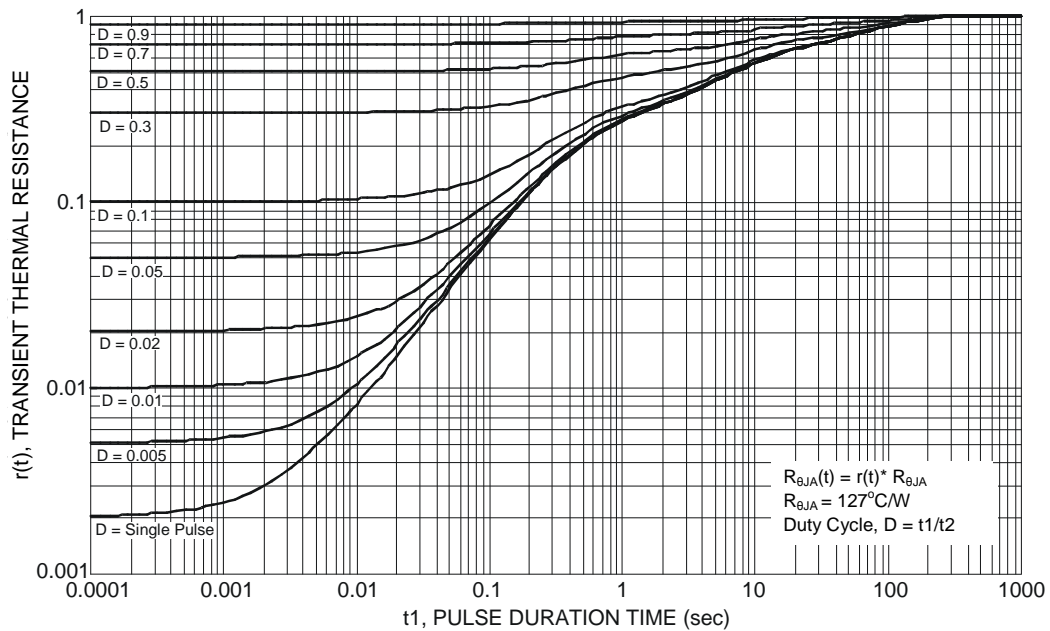
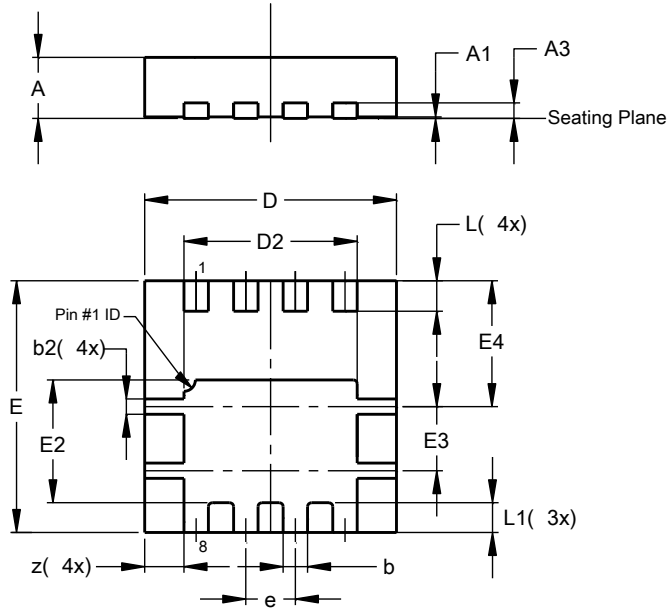


Figure 11 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

POWERDI®3333-8

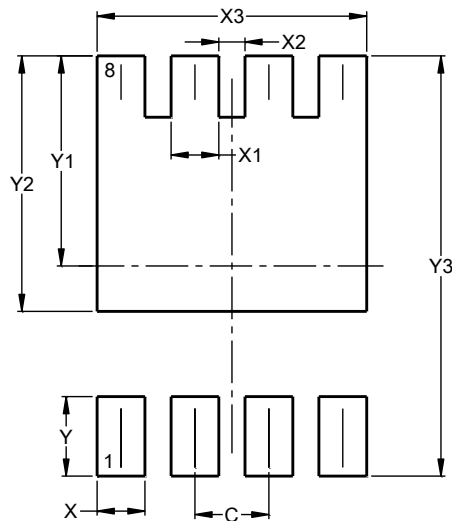


| POWERDI®3333-8 | | | |
|----------------------|------|------|-------|
| Dim | Min | Max | Typ |
| A | 0.75 | 0.85 | 0.80 |
| A1 | 0.00 | 0.05 | 0.02 |
| A3 | — | — | 0.203 |
| b | 0.27 | 0.37 | 0.32 |
| b2 | 0.15 | 0.25 | 0.20 |
| D | 3.25 | 3.35 | 3.30 |
| D2 | 2.22 | 2.32 | 2.27 |
| E | 3.25 | 3.35 | 3.30 |
| E2 | 1.56 | 1.66 | 1.61 |
| E3 | 0.79 | 0.89 | 0.84 |
| E4 | 1.60 | 1.70 | 1.65 |
| e | — | — | 0.65 |
| L | 0.35 | 0.45 | 0.40 |
| L1 | — | — | 0.39 |
| z | — | — | 0.515 |
| All Dimensions in mm | | | |

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

POWERDI®3333-8



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 0.650 |
| X | 0.420 |
| X1 | 0.420 |
| X2 | 0.230 |
| X3 | 2.370 |
| Y | 0.700 |
| Y1 | 1.850 |
| Y2 | 2.250 |
| Y3 | 3.700 |

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